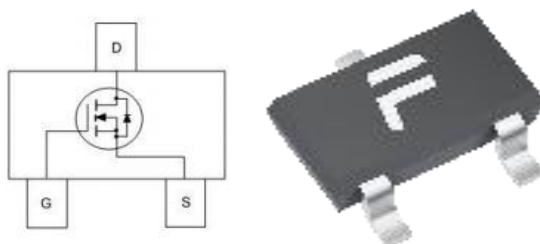


SOT-323 50V N Channel Enhancement 沟道增强型
MOS Field Effect Transistor 场效应管



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	50	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ\text{C}$)	200	mA
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	1	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ\text{C}$)	300	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ\text{C}$

■ Electrical Characteristics 电特性

 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	50	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	0.5	1.0	1.5	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =50V)	I _{DSS}	—	—	0.5	uA
Gate Body Leakage 栅极漏电流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =200mA, V _{GS} =10V)	R _{DS(ON)}	—	—	3.5	Ω
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{ISS}	—	30	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{OSS}	—	8	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{RSS}	—	3	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =25V, I _D =200mA, V _{GS} =10V)	Q _g	—	1.7	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =25V, I _D =200mA, V _{GS} =10V)	Q _{gs}	—	0.47	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =25V, I _D =200mA, V _{GS} =10V)	Q _{gd}	—	0.25	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =25V I _D =200mA, R _{GEN} =6 Ω, V _{GS} =10V)	t _{d(on)}	—	2.6	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =25V I _D =200mA, R _{GEN} =6 Ω, V _{GS} =10V)	t _r	—	19	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =25V I _D =200mA, R _{GEN} =6 Ω, V _{GS} =10V)	t _{d(off)}	—	9.6	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =25V I _D =200mA, R _{GEN} =6 Ω, V _{GS} =10V)	t _f	—	49	—	ns

■ Typical Characteristic Curve 典型特性曲线

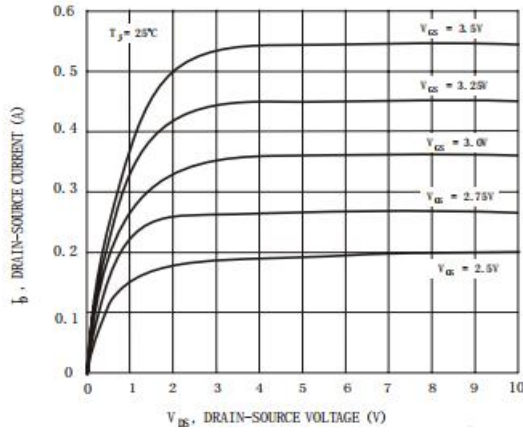


Figure 1: Output Characteristics

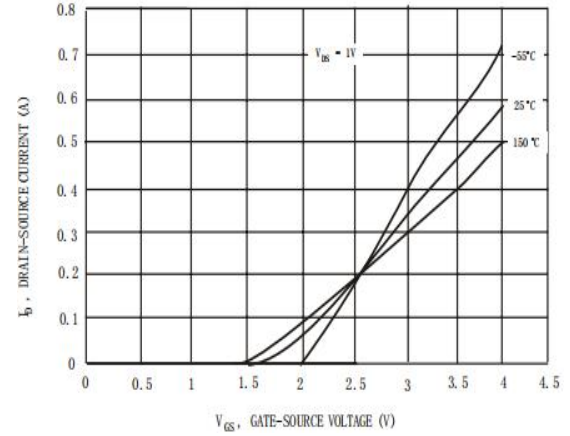


Figure 2: Transfer Characteristics

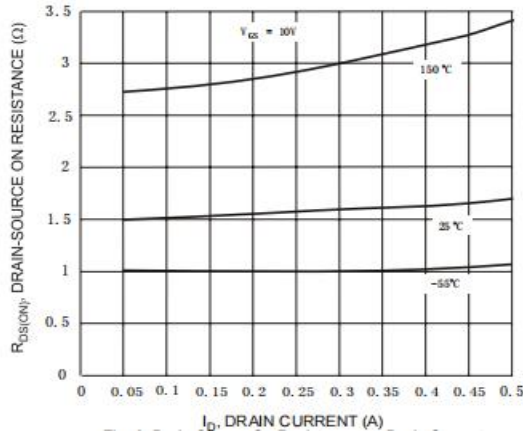


Figure 3: On-Resistance vs. Drain Current

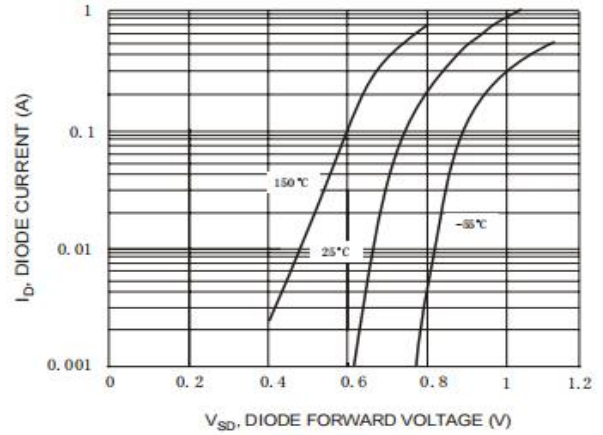


Figure 4: Diode Characteristics

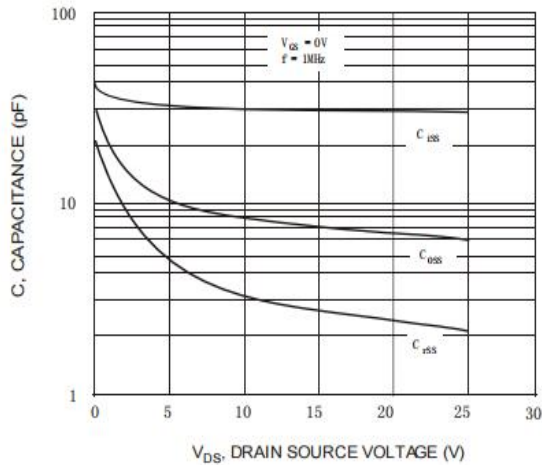


Figure 5: Capacitance Characteristics

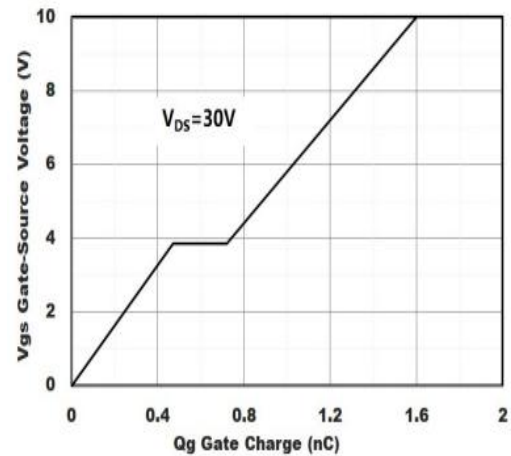
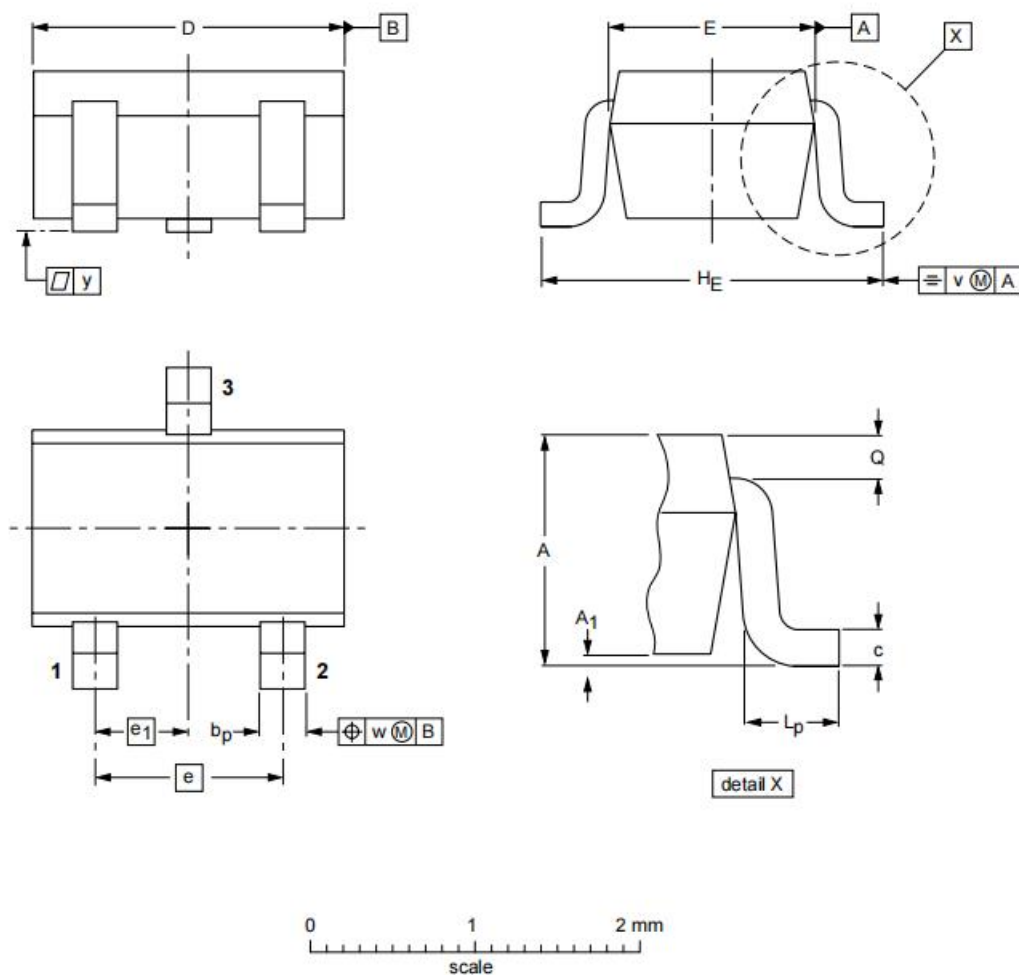


Figure 6: Gate-Charge Characteristics

■ Dimension 外形封装尺寸



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2